

ABSTRACT OF THE DISCLOSURE

A quarter wavelength transmission line is provided between a signal transmission line for transmitting a high frequency signal and a ground node. The quarter wavelength transmission line has a length equal to a quarter of an effective wavelength of an operation frequency of a semiconductor device. A surge absorbing element is connected between the quarter wavelength transmission line and an internal circuit. The signal transmission line is coupled to the internal circuit through a capacitor. A clamp circuit is provided between a power supply line and a ground line. The clamp circuit clamps the voltage difference between the power supply line and the ground line to a prescribed voltage level or less. A high frequency semiconductor device is thus implemented which is capable of preventing breakdown of an internal circuit element due to an electrostatic discharge phenomenon (ESD) without degrading high frequency characteristics.